SMALLBLOCK™ Low Voltage Bias Stabilizer

- Maintains Stable Bias Current in Various Discrete Bipolar Junction and Field Effect Transistors
- Provides Stable Bias Using a Single Component Without Use of Emitter Ballast and Bypass Components

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- Operates Over a Wide Range of Supply Voltages Down to 1.8 Vdc
- Reduces Bias Current Variation Due to Temperature and Unit-to-Unit Parametric Changes
- Consumes < 0.5 mW at V_{CC} = 2.75 V

This device provides a reference voltage and acts as a DC feedback element around an external discrete, NPN BJT or N-Channel FET. It allows the external transistor to have its emitter/source directly grounded and still operate with a stable collector/drain DC current. It is primarily intended to stabilize the bias of discrete RF stages operating from a low voltage regulated supply, but can also be used to stabilize the bias current of any linear stage in order to eliminate emitter/source bypassing and achieve tighter bias regulation over temperature and unit variations. This device is intended to replace a circuit of three to six discrete components and is available in a SOT-143 package.

The combination of low supply voltage, low quiescent current drain, and small package make it ideal for portable communications applications such as:

- Cellular Telephones
- Pagers
- PCN/PCS Portables
- PCMCIA RF Modems
- · Cordless Phones
- Broadband Transceivers and Other Portable Wireless Products

MAXIMUM RATINGS

Rating	Symbol Value		Unit	
Power Supply Voltage	Vcc	15	Vdc	
Ambient Operating Temperature Range	TA	-40 to +85	°C	
Storage Temperature Range	T _{stg}	-65 to +150	°C	
Junction Temperature	TJ	150	°C	
Collector Emitter Voltage (Q2)	VCEO	-15	V	

THERMAL CHARACTERISTICS

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Characteristic	Symbol	Max	Unit
Total Device Power Dissipation (FR-5 PCB of $1'' \times 0.75'' \times 0.062''$, $T_A = 25^{\circ}C$)	PD	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W

DEVICE MARKING

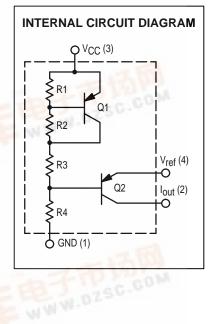
MDC5000T1 = E5

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MDC5000T1

SILICON SMALLBLOCK™ INTEGRATED CIRCUIT





ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Recommended Operating Supply Voltage	VCC	1.8	2.75	10	Volts
Power Supply Current (V _{CC} = 2.75 V) V _{ref} , I _{out} are unterminated See Figure 8	ICC	_	110	200	μΑ
Q2 Collector Emitter Breakdown Voltage (I _{C2} = 10 μA, I _{B2} = 0)	V(BR)CEO2	-15			Volts
Reference Voltage (V _{CC} = 2.75 V, V _{out} = 0.7 V) (I_{out} = 30 μ A) (I_{out} = 150 μ A) See Figure 9	Vref	2.010 2.075	2.035 2.100	2.060 2.125	Volts
Reference Voltage (V _{CC} = 2.75 V, V _{Out} = 0.7 V, -40° C \leq T _A \leq +85°C) V _{CC} Pulse Width = 10 mS, Duty Cycle = 1.0% (I _{out} = 10 μ A) (I _{out} = 30 μ A) (I _{out} = 100 μ A) See Figure 9	ΔV _{ref}		±5 ±12 ±25	±10 ±25 ±50	mV

TYPICAL OPEN LOOP CHARACTERISTICS

(Refer to Circuit of Figure 9)

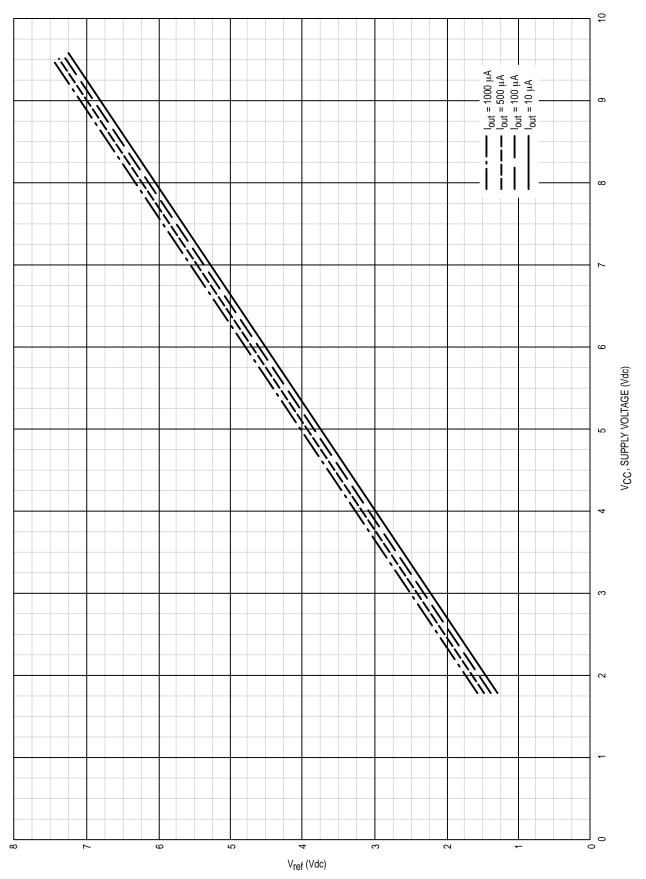


Figure 1. V_{ref} versus $V_{CC} @ I_{out}$

TYPICAL OPEN LOOP CHARACTERISTICS

(Refer to Circuits of Figures 8, 10 & 11)

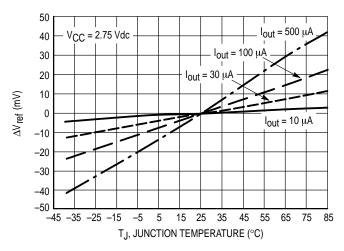


Figure 2. ΔV_{ref} versus TJ @ I_{out}

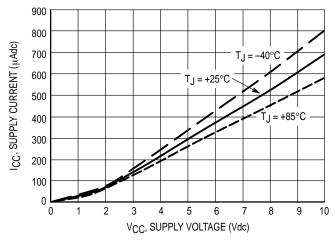


Figure 3. ICC versus VCC @ TJ

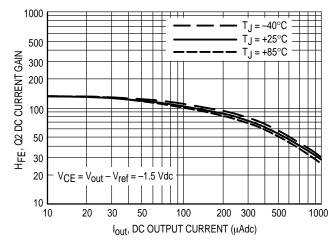
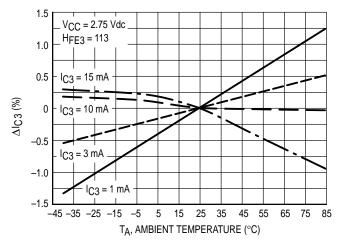


Figure 4. Q2 Current Gain versus Output Current

TYPICAL CLOSED LOOP PERFORMANCE

(Refer to Circuits of Figures 12 & 13)



4.0 $V_{CC} = 2.75 \text{ Vdc}$ $T_A = 25^{\circ}C$ $I_{C3} = 15 \text{ mA}$ 3.0 $I_{C3} = 10 \text{ mA}$ $I_{C3} = 3 \text{ mA}$ 2.0 $I_{C3} = 1 \text{ mA}$ W ref (%) 1.0 0 -1.0-2.0 -3.0 L 50 100 150 200 250 300 350 H_{FE}, EXTERNAL TRANSISTOR DC BETA

Figure 5. ΔI_{C3} versus $T_A @ I_{C3}$

Figure 6. ΔV_{ref} versus External Transistor DC Beta @ IC3

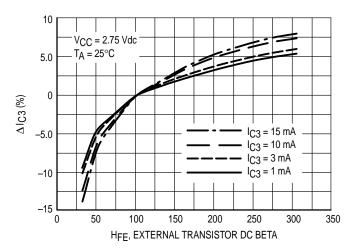


Figure 7. ΔI_{C3} versus External Transistor DC Beta @ I_{C3}

OPEN LOOP TEST CIRCUITS

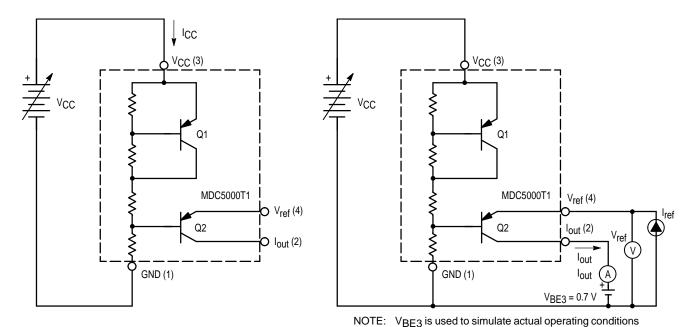
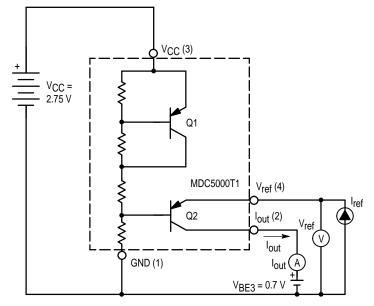


Figure 8. ICC versus VCC Test Circuit

that reduce V_{CE2} & H_{FE2}, and increase I_{B2} & V_{ref}.

Figure 9. $V_{\mbox{ref}}$ versus $V_{\mbox{CC}}$ Test Circuit



NOTE: V_{BE3} is used to simulate actual operating conditions that reduce V_{CE2} & H_{FE2} , and increase I_{B2} & $V_{ref.}$

Figure 10. V_{ref} versus T_J Test Circuit

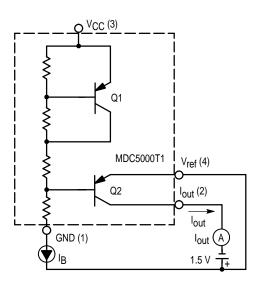


Figure 11. HFE versus I_{out} Test Circuit

CLOSED LOOP TEST CIRCUITS

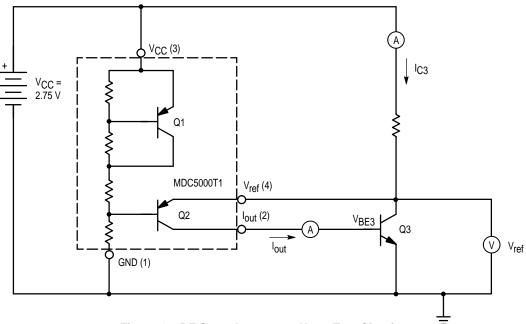


Figure 12. RF Stage IC3 versus HFE3 Test Circuit

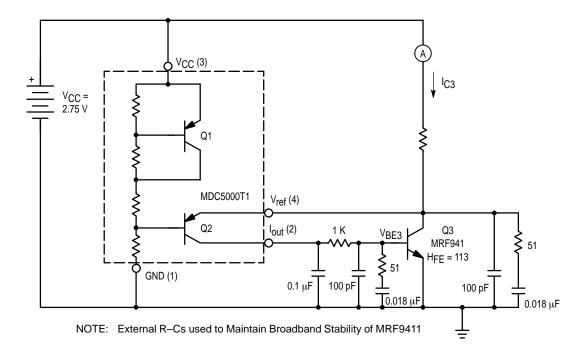
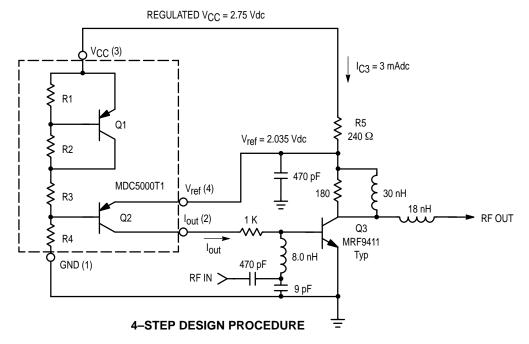
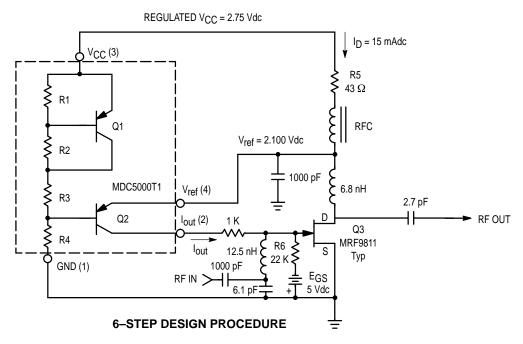


Figure 13. RF Stage I_{C3} versus T_A Test Circuit



- Step 1: Choose V_{CC} (1.8 V Min to 10 V Max)
- Step 2: Choose bias current, I_{C3} , and calculate needed I_{out} from typ H_{FE3}
- Step 3: From Figure 1, read $V_{\mbox{ref}}$ for $V_{\mbox{CC}}$ & $I_{\mbox{out}}$ calculated.
- Step 4: Calculate Nominal R5 = ($V_{CC} V_{ref}$) ÷ ($I_{C3} + I_{out}$). Tweak as desired.

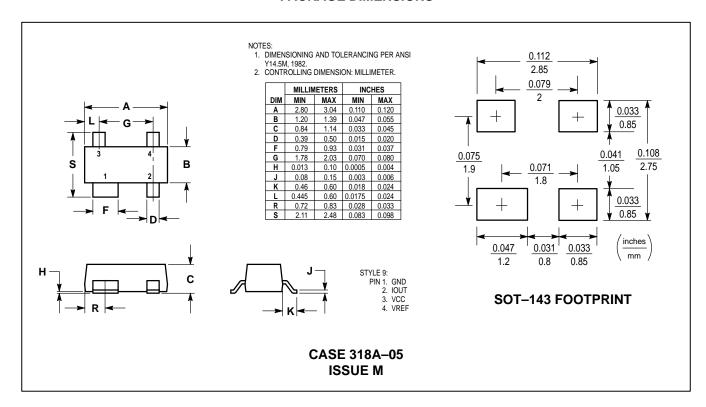
Figure 14. Class A Biasing of a Typical 900 MHz
BJT Amplifier



- Step 1: Choose V_{CC} (1.8 V Min to 10 V Max)
- Step 2: Choose bias current, ID, and determine needed gate-source voltage, VGS.
- Step 3: Choose I_{Out} keeping in mind that too large an I_{Out} can impair MDC5000T1 $\Delta V_{ref}/\Delta T_{J}$ performance (Figure 2) but too large an R6 can cause I_{DGO} & I_{GSO} to bias on the FET.
- Step 4: Calculate R6 = $(V_{GS} + E_{GS}) \div I_{out}$
- Step 5: From Figure 1, read V_{ref} for V_{CC} & I_{out} chosen
- Step 6: Calculate Nominal R5 = $(V_{CC} V_{ref}) \div (I_D + I_{out})$. Tweak as desired.

Figure 15. Class A Biasing of a Typical 890 MHz
Depletion Mode GaAs FET Amplifier

PACKAGE DIMENSIONS



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